

is also unavailable for Kelvin measurement. The impedance of each of the segments of the stress migration test structure except the two end segments are known. The impedance of the first and last segments of the stress migration test structure may be ignored in subsequent calculations.--

IN THE CLAIMS

Please amend the claims as follows:

1. (Amended) A wafer, comprising:

at least two die areas formed on the wafer, the at least two die areas defining a street therebetween; and

a stress migration test structure in the street, the stress migration test structure comprising a conductive runner having a length sufficient to develop axial stress above the threshold for nucleating voids for the technology in which the runner is fabricated, the conductive runner having a plurality of taps at uniform impedance intervals along the runner, the taps spaced along the runner such that the variation of the impedance of the runner between adjacent taps, due to the presence of a stress migration void in the runner is a detectable portion of the impedance between the adjacent taps absent stress migration voids.

2. (Amended) A wafer, comprising:

at least four die areas formed on the wafer, the at least four die areas defining two intersecting streets thereamong; and

a stress migration test structure in a region of the two intersecting streets proximate the at least four die areas and comprising a conductive runner having a length sufficient to develop axial stress above the threshold for nucleating voids for the technology in which the runner is fabricated, the conductive runner having a plurality of taps at uniform impedance intervals along the runner, the taps spaced along the runner such that the variation of the impedance of the runner between adjacent taps, due to the presence of a stress migration void in the runner is a detectable portion of the impedance between the adjacent taps absent stress migration voids.

--42. A stress migration test device, comprising:

*Cont'd 43*  
a conductive runner, the conductive runner having a length sufficient to develop axial stress above a threshold for nucleating voids for a technology in which the runner is fabricated, wherein the conductive runner is comprised of two conductive materials providing parallel conduction paths of different impedances.

43. A stress migration test device, comprising:

a conductive runner, the conductive runner having a length sufficient to develop axial stress above a threshold for nucleating voids for a technology in which the runner is fabricated, wherein the conductive runner serpentine back and forth boustrophedonically on a common plane.--

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